

## ABSTRACT OF DISCLOSURE

A method including the steps of: consecutively  
5 depositing a first etch stop layer, a first compound semiconductor and a second compound semiconductor layer overlying a semiconductor substrate, the first etch stop layer, the first and second compound semiconductor layers having different compositions from one another,  
10 etching the first and second compound semiconductor layers until the etching stops at the first etch stop layer, and forming a semiconductor laser device including the first etch stop layer and the first and second compound semiconductor layers. The existence of the first  
15 compound semiconductor layer made of a material different from those of the second compound semiconductor layer and the etch stop layer enables the etching of the second compound semiconductor layer while controlling the etching depth thereof by using the  
20 etch stop layer.

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